IN THE CLAIMS

1. (currently amended): A method of fabricating a protective film comprising:

providing a vacuum ultraviolet radiation CVD (Chemical Vapor Deposition) system comprising a vacuum ultraviolet rays generator, a reactor provided with a platform for supporting a substrate, a heat retainer provided on the platform, and a window separating the vacuum ultraviolet rays generator from the reactor;

feeding an organic stock gas from a gas feeder into the reactor while retaining temperature of the substrate at a temperature about equal to or less than 100 °C with the heat retainer; and

irradiating simultaneously the reactor with vacuum ultraviolet rays from the vacuum ultraviolet rays generator through the window;

wherein photons from the vacuum ultraviolet ray generator have a wavelength of about 172 nm and an energy of about 7.2 eV, sufficient to break an Si-N bond.

2. (previously presented): A method of fabricating a protective film according to claim 1, wherein retaining of the temperature with the heat retainer is carried out such that the temperature of the substrate is kept at a low temperature in a range of about 25 °C to 100 °C.

3. (original): The method of fabricating a protective film according to claim 1, wherein an organosilazane gas having Si-N bonds is used for the organic stock gas.

4. (original): The method of fabricating a protective film according to claim 1, further comprising adding an additive gas for increasing nitrogen content in the protective film, or a regulator gas for use in regulating a partial pressure of the organic stock gas in the reactor to the organic stock gas so as to be fed from the gas feeder into the reactor.

5. (canceled)

6. (currently amended): The method of fabricating a protective film according to claim [[5]] 1, wherein the step of providing the ultraviolet rays generator includes providing a xenon excimer lamp.